

**AMENDMENTS TO THE CLAIMS**

**Listing of the claims:**

Following is a listing of all claims in the present application, which listing supersedes all previously presented claims:

1. (Currently Amended) A surface acoustic wave device comprising:  
a pair of reflective electrodes formed on a single-crystal piezoelectric substrate;  
and  
at least one set of comb electrodes formed between the pair of reflective electrodes, each comb electrode constituting the comb electrode set including:  
a plurality of electrode fingers; and  
a bus bar connecting the plurality of electrode fingers in common, wherein,  
the electrode fingers of one comb electrode are laid in a state of being inserted to  
the electrode fingers of the other comb electrode, and a thick film thicker than  
each of the plurality of electrode fingers is produced in a partial area of the bus  
bar, and a tip gap is provided between the top of each plurality of electrode  
fingers and the end face of the opposed bus bar, with a distance therebetween  
set not greater than  $0.2\lambda$ , ~~[[()]]~~where~~[[,]]~~  $\lambda$  is one period of the comb electrode~~[[()]]~~.
2. (Currently Amended) A surface acoustic wave device comprising:  
a pair of reflective electrodes formed on a single-crystal piezoelectric substrate;  
and

at least one set of comb electrodes formed between the pair of reflective electrodes, each comb electrode constituting the comb electrode set including:

a plurality of electrode fingers and a plurality of dummy electrodes disposed alternately; and

a bus bar connecting the plurality of electrode fingers and the plurality of dummy electrodes in common, wherein the electrode fingers of one comb electrode are laid in a state of being inserted to the electrode fingers of the other comb electrode, a thick film thicker than each of the plurality of electrode fingers is produced in partial areas of the bus bar, and a tip gap is provided between the top of each plurality of electrode fingers and the top of the opposed dummy electrode, with a distance therebetween set not greater than  $0.2\lambda$ , where  $\lambda$  is one period of the comb electrode.

3. (Currently Amended) A surface acoustic wave device comprising:  
a pair of reflective electrodes formed on a single-crystal piezoelectric substrate;  
and

three sets of comb electrodes formed between the pair of reflective electrodes, each comb electrode constituting the comb electrode set including:

a plurality of electrode fingers and a plurality of dummy electrodes disposed alternately; and

a bus bar connecting the plurality of electrode fingers and the plurality of dummy electrodes in common, wherein the electrode fingers of one comb electrode are laid in a state of being inserted to the electrode fingers of the other

comb electrode, a thick film thicker than each of the plurality of electrode fingers is produced in partial areas of the bus bar, and a tip gap is provided between the top of each plurality of electrode fingers and the top of the opposed dummy electrode, with a distance therebetween set not greater than  $0.2\lambda$ , where  $\lambda$  is one period of the comb electrode.

4. (Currently Amended) A surface acoustic wave device comprising a plurality of resonators connected into a ladder shape, each resonator including:  
a pair of reflective electrodes formed on a single-crystal piezoelectric substrate;  
and

at least one set of comb electrodes formed between the pair of reflective electrodes, each comb electrode of the comb electrode set constituting the resonator having:

a plurality of electrode fingers and a plurality of dummy electrodes disposed alternately; and

a bus bar connecting the plurality of electrode fingers and the plurality of dummy electrodes in common, wherein the electrode fingers of one comb electrode are laid in a state of being inserted to the electrode fingers of the other comb electrode, a thick film thicker than each of the plurality of electrode fingers is produced in partial areas of the bus bar, and a tip gap is provided between the top of each plurality of electrode fingers and the top of the opposed dummy electrode, with a distance therebetween set not greater than  $0.2\lambda$ , where  $\lambda$  is one period of the comb electrode.

5. (Currently Amended) A surface acoustic wave device comprising a plurality of resonators connected into a lattice shape, each resonator including:  
a pair of reflective electrodes formed on a single-crystal piezoelectric substrate;  
and  
at least one set of comb electrodes formed between the pair of reflective electrodes, each comb electrode of the comb electrode set constituting the resonator having:  
a plurality of electrode fingers and a plurality of dummy electrodes disposed alternately; and  
a bus bar connecting the plurality of electrode fingers and the plurality of dummy electrodes in common, wherein the electrode fingers of one comb electrode are laid in a state of being inserted to the electrode fingers of the other comb electrode, a thick film thicker than each of the plurality of electrode fingers is produced in partial areas of the bus bar, and a tip gap is provided between the top of each plurality of electrode fingers and the top of the opposed dummy electrode, with a distance therebetween set not greater than  $0.2\lambda$ , where  $\lambda$  is one period of the comb electrode.

6. (Currently Amended) A surface acoustic wave device comprising:  
a pair of reflective electrodes formed on a single-crystal piezoelectric substrate;  
and  
three sets of comb electrodes formed between the pair of reflective electrodes, each comb electrode forming the comb electrode set including:

a plurality of electrode fingers; and

a bus bar connecting the plurality of electrode fingers in common, wherein, the electrode fingers of one comb electrode are laid in a state of being inserted to the electrode fingers of the other comb electrode, and a thick ~~Thick~~ film thicker than each plurality of electrode fingers is produced in partial areas of the bus bar, and a tip gap is provided between the top of each plurality of electrode fingers and the end face of the opposed bus bar, with a distance therebetween set not greater than  $0.2\lambda$ , ~~where  $\lambda$  is one period of the comb electrode~~.

7. (Currently Amended) A surface acoustic wave device comprising a plurality of resonators connected into a ladder shape, each resonator including:  
a pair of reflective electrodes formed on a single-crystal piezoelectric substrate;  
and  
at least one set of comb electrodes formed between the pair of reflective electrodes, each comb electrode of the comb electrode set constituting the resonator having:

a plurality of electrode fingers; and

a bus bar connecting the plurality of electrode fingers in common, wherein, the electrode fingers of one comb electrode are laid in a state of being inserted to the electrode fingers of the other comb electrode, and a thick ~~Thick~~ film thicker than each plurality of electrode fingers is produced in partial areas of the bus bar, and a tip gap is provided between the top of each plurality of electrode fingers

and the end face of the opposed bus bar, with a distance therebetween set not greater than  $0.2\lambda$ , where  $\lambda$  is one period of the comb electrode.

8. (Currently Amended) A surface acoustic wave device comprising a plurality of resonators connected into a lattice shape, each resonator including:
- a pair of reflective electrodes formed on a single-crystal piezoelectric substrate;
  - and
  - at least one set of comb electrodes formed between the pair of reflective electrodes, each comb electrode of the comb electrode set constituting the resonator having:
    - a plurality of electrode fingers; and
    - a bus bar connecting the plurality of electrode fingers in common, wherein, the electrode fingers of one comb electrode are laid in a state of being inserted to the electrode fingers of the other comb electrode, and a thick ~~Thick~~ film thicker than each plurality of electrode fingers is produced in partial areas of the bus bar, and a tip gap is provided between the top of each plurality of electrode fingers and the end face of the opposed bus bar, with a distance therebetween set not greater than  $0.2\lambda$ , where  $\lambda$  is one period of the comb electrode.

9. (Canceled)

10. (Original) The surface acoustic wave device according to claim 3 or claim 6, wherein, a ratio  $L/S$  of an electrode width  $L$  of the electrode finger to a space  $S$  between neighboring electrode fingers is set to between 0.6 and 0.8.

11. (Currently Amended) The surface acoustic wave device according to any ~~either one of claims claim 1 and 6-8 ~~claims 6 to 8~~~~, wherein, each partial area of the bus bar in which the thick film is produced is disposed with a distance of not greater than  $0.75\lambda$  from the connection end face of the bus bar connecting to each plurality of electrode fingers ~~[[()]]~~where,  $\lambda$  is one period of the comb electrode~~[[()]]~~.

12. (Currently Amended) The surface acoustic wave device according to any ~~either one of claims claim 1 and 6-8 ~~claims 6 to 8~~~~, wherein, the plurality of electrode fingers and the bus bar connecting the electrode fingers is formed of metal of which principal component is aluminum, and each partial area of the bus bar in which the thick film is produced has an additional thickness of not less than  $0.05\lambda$  ~~not smaller than the film thickness of the plurality of electrode fingers (where[[,]]~~  $\lambda$  is one period of the comb electrode~~[[()]]~~.

13. (Currently Amended) The surface acoustic wave device according to claim 12, wherein, ~~preferably~~, each partial area of the bus bar in which the thick film is produced has an additional thickness of not greater than  $0.35\lambda$  ~~not greater than the film thickness of the plurality of electrode fingers (where[[,]]~~  $\lambda$  is one period of the comb electrode~~[[()]]~~.

14. (Currently Amended) The surface acoustic wave device according to any ~~either one of claims claim 1 and 6-8 claims 6 to 8~~, wherein each partial area of the bus bar in which the thick film is produced is formed of heavy metal.

15. (Currently Amended) The surface acoustic wave device according to any ~~either one of claims claim 1 and 6-8 claims 6 to 8~~, wherein each partial area of the bus bar in which the thick film is produced is formed of insulating material.

16. (Currently Amended) The surface acoustic wave device according to any ~~either one of claims 1-8 1 to 8~~, wherein the single-crystal piezoelectric substrate is formed of  $\text{LiTaO}_3$  or  $\text{LiNbO}_3$ , and a leaky surface acoustic wave of the substrate is used.